

2N2608, 2N2609

P-Channel Silicon Junction Field-Effect Transistor

- Low-Level Choppers
- Data Switches
- Commutators

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Gate Drain Voltage	-30V
Continuous Forward Gate Current	50 mA
Continuous Device Power Dissipation	300 mW
Power Derating	2 mW/ $^\circ\text{C}$
Storage Temperature Range	-65 $^\circ\text{C}$ to +150 $^\circ\text{C}$

At 25 $^\circ\text{C}$ free air temperature

		2N2608		2N2609		Unit	Test Conditions
		Min	Max	Min	Max		
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	-30		-30		V	$I_G = -1 \mu\text{A}$, $V_{DS} = 0 \text{ V}$
Gate Reverse Current	I_{GSS}		10		30	nA	$V_{GS} = 10 \text{ V}$, $V_{DS} = 0 \text{ V}$
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	1	4	1	4	V	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$
Drain Saturation Current (pulsed)	I_{DSS}	-0.9	-4.5	-2	-10	mA	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$

Dynamic Electrical Characteristics

Common-Source Forward Transconductance	g_{fs}	1		25		mS	$V_{DS} = -10 \text{ V}$, $V_{GS} = 0 \text{ V}$	f = 1 kHz
Common-Source Input Capacitance	C_{iss}		17		30	pF	$V_{DS} = -10 \text{ V}$, $V_{GS} = 1 \text{ V}$	f = 1 MHz
Common-Source Reverse Transfer Capacitance	C_{rss}		5		7	pF	$V_{DS} = 10 \text{ V}$, $I_D = 5 \text{ mA}$	f = 1 MHz

Typical

Equivalent Short Circuit Input Noise Voltage	$\sim e_N$	10		10		nV/ $\sqrt{\text{Hz}}$	$V_{DS} = 10 \text{ V}$, $I_D = 5 \text{ mA}$	f = 1 kHz
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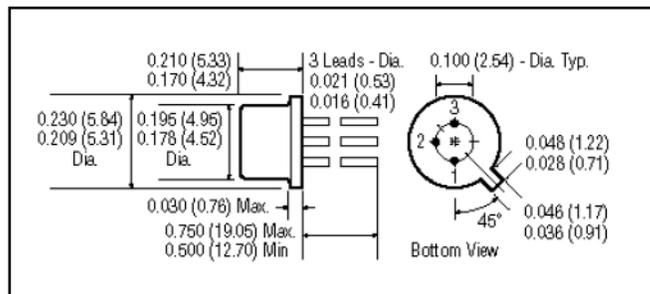
TO-18 Package

Dimensions in Inches (mm)

Pin Configuration

1 Source 1, 2 Gate & Case, 3 Drain

Surface Mount - SMP2608, SMP2609



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